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TRANSMITTAL FORM (to be used for all correspondence after initial filing)			ation Number	09/827,056
			Date	April 3, 2001
			First Named Inventor Liu, Chun-Mai	
			Art Unit 2811	
		Examiner Name Thomas J. Magee		
Total Number of Pages in This Submission 23		Attorney Docket Number 0187		018757-004600US
ENCLOSURES (Check all that apply)				
Fee Transmittal Form	Drawing(s)			After Allowance Communication to Group
Fee Attached	Licensing-related Papers			Appeal Communication to Board of Appeals and Interferences
Amendment / Reply	Petition			Appeal Communication to Group (Appeal Notice, Brief, Reply Brief)
After Final	Petition to Convert to a Provisional Application			Proprietary Information
Affidavits/declaration(s)	Power of Attorney, Revocation Change of Correspondence Address			Status Letter
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Certified Copy of Priority Document(s)	Remarks The Commissioner is Deposit Account 20-1			authorized to charge any additional fees to 330.
Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53		e to the Office Action mailed 12/30/02, please make the enclosed of record.		
SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT				
Firm Townsend and Townsend and Crew LLP or Individual Reg. No. 37,692				
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TOWNSEND and TOWNSEND and CREW LLP

10/B(N.E) J. Steptan 3-21-03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Examiner:

Thomas J. Magee

Chun-Mai Liu et al.

Art Unit:

2811

Application No.: 09/827,056

AMENDMENT

Filed: April 3, 2001

For: METHOD OF FABRICATING HIGH-COUPLING RATIO SPLIT GATE FLASH MEMORY CELL ARRAY

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

In response to the Office Action mailed 12/30/02, please amend the aboveidentified application as follows:

IN THE CLAIMS:

Please amend the claims 1, 5, 6, 12 and 14 as follows:

1. (Twice amended) A method of fabricating a flash memory device including an array of split-gate cells, comprising the steps of:

providing a silicon substrate having a top surface;

forming a common source region in an area of said top surface for each pair of said cells;

implanting ions into predefined areas of each said common source region;